Features

- **Serial Peripheral Interface (SPI) Compatible**
- **Supports SPI Modes 0 (0,0) and 3 (1,1)**
- **Low-voltage and Standard-voltage Operation**
  - **– 2.7 (V_{CC} = 2.7V to 5.5V)**
  - **– 1.8 (V_{CC} = 1.8V to 5.5V)**
- **3 MHz Clock Rate**
- **64-byte Page Mode and Byte Write Operation**
- **Block Write Protection**
  - **– Protect 1/4, 1/2, or Entire Array**
- **Write Protect ($\overline{WP}$) Pin and Write Disable Instructions for Both Hardware and Software Data Protection**
- **Self-timed Write Cycle (5 ms Typical)**
- **High-reliability**
  - **– Endurance: 100,000 Write Cycles**
  - **– Data Retention: >200 Years**
- **Automotive Grade and Extended Temperature Devices Available**
- **8-lead PDIP, 8-lead EIAJ SOIC, 8-lead and 16-lead JEDEC SOIC, 14-lead and 20-lead TSSOP, 8-lead Leadless Array and 8-ball dBGA™ Packages**
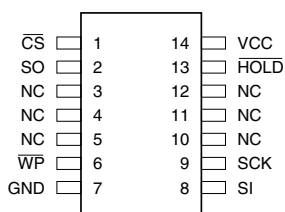
Description

The AT25128/256 provides 131,072/262,144 bits of serial electrically-erasable programmable read only memory (EEPROM) organized as 16,384/32,768 words of 8 bits each. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. The devices are available in space saving 8-lead PDIP (AT25128/256), 8-lead EIAJ SOIC (AT25128/256), 8-lead
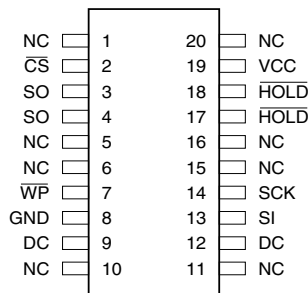
(continued)

SPI Serial EEPROMs

128K (16,384 x 8)

256K (32,768 x 8)

AT25128
AT25256

Pin Configurations

Pin Name	Function
$\overline{CS}$	Chip Select
SCK	Serial Data Clock
SI	Serial Data Input
SO	Serial Data Output
GND	Ground
VCC	Power Supply
$\overline{WP}$	Write Protect
$\overline{HOLD}$	Suspends Serial Input
NC	No Connect
DC	Don't Connect

14-lead TSSOP

$\overline{CS}$	1	14	VCC
SO	2	13	$\overline{HOLD}$
NC	3	12	NC
NC	4	11	NC
NC	5	10	NC
$\overline{WP}$	6	9	SCK
GND	7	8	SI

20-lead TSSOP*

NC	1	20	NC
$\overline{CS}$	2	19	VCC
SO	3	18	$\overline{HOLD}$
SO	4	17	$\overline{HOLD}$
NC	5	16	NC
NC	6	15	NC
$\overline{WP}$	7	14	SCK
GND	8	13	SI
DC	9	12	DC
NC	10	11	NC

8-ball dBGA

VCC	⑧	①	$\overline{CS}$
$\overline{HOLD}$	⑦	②	SO
SCK	⑥	③	$\overline{WP}$
SI	⑤	④	GND
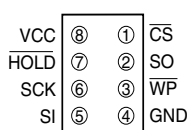
Bottom View

8-lead Leadless Array

VCC	8	1	$\overline{CS}$
$\overline{HOLD}$	7	2	SO
SCK	6	3	$\overline{WP}$
SI	5	4	GND

Bottom View

16-lead SOIC

$\overline{CS}$	1	16	VCC
SO	2	15	$\overline{HOLD}$
NC	3	14	NC
NC	4	13	NC
NC	5	12	NC
NC	6	11	NC
$\overline{WP}$	7	10	SCK
GND	8	9	SI

8-lead PDIP

$\overline{CS}$	1	8	VCC
SO	2	7	$\overline{HOLD}$
$\overline{WP}$	3	6	SCK
GND	4	5	SI

8-lead SOIC

$\overline{CS}$	1	8	VCC
SO	2	7	$\overline{HOLD}$
$\overline{WP}$	3	6	SCK
GND	4	5	SI
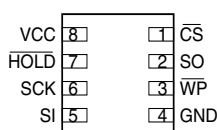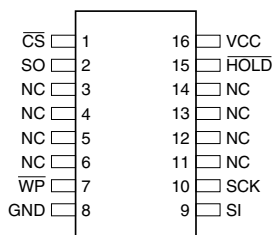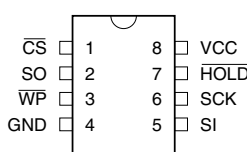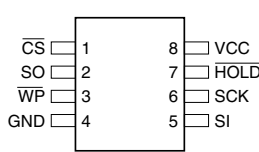
*Note: Pins 3, 4 and 17, 18 are internally connected for 14-lead TSSOP socket compatibility.

and 16-lead JEDEC SOIC (AT25128), 14-lead TSSOP (AT25128), 20-lead TSSOP (AT25128/256), 8-lead Leadless Array (AT25256), and 8-ball dBGA packages. In addition, the entire family is available in 2.7V (2.7V to 5.5V) and 1.8V (1.8V to 5.5V) versions.

The AT25128/256 is enabled through the Chip Select pin ($\overline{CS}$) and accessed via a 3-wire interface consisting of Serial Data Input (SI), Serial Data Output (SO), and Serial Clock (SCK). All programming cycles are completely self-timed, and no separate ERASE cycle is required before WRITE.

BLOCK WRITE protection is enabled by programming the status register with top ¼, top ½ or entire array of write protection. Separate program enable and program disable instructions are provided for additional data protection. Hardware data protection is provided via the $\overline{WP}$ pin to protect against inadvertent write attempts to the status register. The $\overline{HOLD}$ pin may be used to suspend any serial communication without resetting the serial sequence.

Absolute Maximum Ratings*

Operating Temperature................................... -55°C to +125°C
Storage Temperature..................................... -65°C to +150°C
Voltage on Any Pin with Respect to Ground ....-1.0V to +7.0V
Maximum Operating Voltage 6.25V
DC Output Current.. 5.0 mA

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Block Diagram
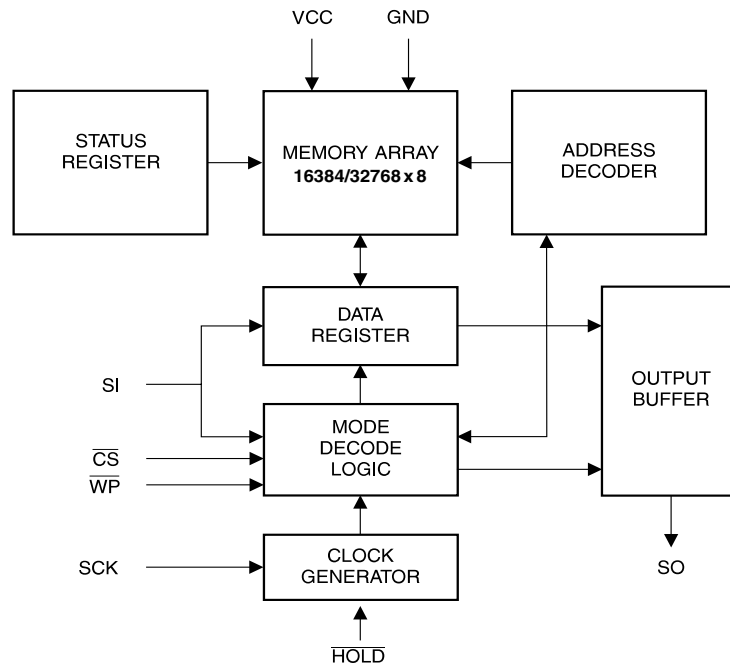
Pin Capacitance[1]

Applicable over recommended operating range from T_A = 25°C, f = 1.0 MHz, V_{CC} = +5.0V (unless otherwise noted).

Symbol	Test Conditions	Max	Units	Conditions
C_{OUT}	Output Capacitance (SO)	8	pF	V_{OUT} = 0V
C_{IN}	Input Capacitance ($\overline{CS}$, SCK, SI, $\overline{WP}$, $\overline{HOLD}$)	6	pF	V_{IN} = 0V

Note: 1.   This parameter is characterized and is not 100% tested.

DC Characteristics

Applicable over recommended operating range from T_{AI} = -40°C to +85°C, V_{CC} = +1.8V to +5.5V,
T_{AC} = 0°C to +70°C, V_{CC} = +1.8V to +5.5V(unless otherwise noted).

Symbol	Parameter	Test Condition		Min	Typ	Max	Units
V_{CC1}	Supply Voltage			1.8		3.6	V
V_{CC2}	Supply Voltage			2.7		5.5	V
V_{CC3}	Supply Voltage			4.5		5.5	V
I_{CC1}	Supply Current	V_{CC} = 5.0V at 1 MHz, SO = Open, Read			2.0	3.0	mA
I_{CC2}	Supply Current	V_{CC} = 5.0V at 2 MHz, SO = Open, Read, Write			3.0	5.0	mA
I_{SB1}	Standby Current	V_{CC} = 1.8V, $\overline{CS}$ = V_{CC}			0.1	2.0	µA
I_{SB2}	Standby Current	V_{CC} = 2.7V, $\overline{CS}$ = V_{CC}			0.2	2.0	µA
I_{SB3}	Standby Current	V_{CC} = 5.0V, $\overline{CS}$ = V_{CC}			2.0	5.0	µA
I_{IL}	Input Leakage	V_{IN} = 0V to V_{CC}		-3.0		3.0	µA
I_{OL}	Output Leakage	V_{IN} = 0V to V_{CC}, T_{AC} = 0°C to 70°C		-3.0		3.0	µA
V_{IL}[1]	Input Low-voltage			-1.0		V_{CC} x 0.3	V
V_{IH}[1]	Input High-voltage			V_{CC} x 0.7		V_{CC} + 0.5	V
V_{OL1}	Output Low-voltage	4.5 ≤ V_{CC} ≤ 5.5V	I_{OL} = 3.0 mA			0.4	V
V_{OH1}	Output High-voltage		I_{OH} = -1.6 mA	V_{CC} - 0.8			V
V_{OL2}	Output Low-voltage	1.8V ≤ V_{CC} ≤ 3.6V	I_{OL} = 0.15 mA			0.2	V
V_{OH2}	Output High-voltage		I_{OH} = -100 µA	V_{CC} - 0.2			V

Note: 1. V_{IL} and V_{IH} max are reference only and are not tested.

AC Characteristics

Applicable over recommended operating range from T_A = -40°C to + 85°C, V_{CC} = As Specified,
CL = 1 TTL Gate and 100 pF (unless otherwise noted).

Symbol	Parameter	Voltage	Min	Max	Units
f_{SCK}	SCK Clock Frequency	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	0 0 0	3.0 2.1 0.5	MHz
t_{RI}	Input Rise Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5		2 2 2	µs
t_{FI}	Input Fall Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5		2 2 2	µs
t_{WH}	SCK High Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	150 200 800		ns
t_{WL}	SCK Low Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	150 200 800		ns
t_{CS}	$\overline{CS}$ High Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	250 250 1000		ns
t_{CSS}	$\overline{CS}$ Setup Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	100 250 1000		ns
t_{CSH}	$\overline{CS}$ Hold Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	150 250 1000		ns
t_{SU}	Data In Setup Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	30 50 100		ns
t_H	Data In Hold Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	50 50 100		ns
t_{HD}	$\overline{Hold}$ Setup Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	100 100 400		ns
t_{CD}	$\overline{Hold}$ Hold Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	200 300 400		ns
t_V	Output Valid	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	0 0 0	150 200 800	ns
t_{HO}	Output Hold Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	0 0 0		ns
t_{LZ}	$\overline{Hold}$ to Output Low Z	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5	0 0 0	100 200 300	ns

AC Characteristics (Continued)

Applicable over recommended operating range from T_A = -40°C to + 85°C, V_{CC} = As Specified,
CL = 1 TTL Gate and 100 pF (unless otherwise noted).

Symbol	Parameter	Voltage	Min	Max	Units
t_{HZ}	$\overline{Hold}$ to Output High Z	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5		100 200 300	ns
t_{DIS}	Output Disable Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5		200 250 1000	ns
t_{WC}	Write Cycle Time	4.5 - 5.5 2.7 - 5.5 1.8 - 5.5		5 10 10	ms
Endurance[1]	5.0V, 25°C, Page Mode		100K		Write Cycles

Note: 1. This parameter is characterized and is not 100% tested. Contact Atmel for further information.

Serial Interface Description

MASTER: The device that generates the serial clock.

SLAVE: Because the Serial Clock pin (SCK) is always an input, the AT25128/256 always operates as a slave.

TRANSMITTER/RECEIVER: The AT25128/256 has seperate pins designated for data transmission (SO) and reception (SI).

MSB: The Most Significant Bit (MSB) is the first bit transmitted and received.

SERIAL OP-CODE: After the device is selected with $\overline{CS}$ going low, the first byte will be received. This byte contains the op-code that defines the operations to be performed.

INVALID OP-CODE: If an invalid op-code is received, no data will be shifted into the AT25128/256, and the serial output pin (SO) will remain in a high impedance state until the falling edge of $\overline{CS}$ is detected again. This will reinitialize the serial communication.

CHIP SELECT: The AT25128/256 is selected when the $\overline{CS}$ pin is low. When the device is not selected, data will not be accepted via the SI pin, and the serial output pin (SO) will remain in a high impedance state.

HOLD: The $\overline{HOLD}$ pin is used in conjunction with the $\overline{CS}$ pin to select the AT25128/256. When the device is selected and a serial sequence is underway, $\overline{HOLD}$ can be used to pause the serial communication with the master device without resetting the serial sequence. To pause, the $\overline{HOLD}$ pin must be brought low while the SCK pin is low. To resume serial communication, the $\overline{HOLD}$ pin is brought high while the SCK pin is low (SCK may still toggle during $\overline{HOLD}$). Inputs to the SI pin will be ignored while the SO pin is in the high impedance state.

WRITE PROTECT: The write protect pin ($\overline{WP}$) will allow normal read/write operations when held high. When the $\overline{WP}$ pin is brought low and WPEN bit is "1", all write operations to the status register are inhibited. $\overline{WP}$ going low while $\overline{CS}$ is still low will interrupt a write to the status register. If the internal write cycle has already been initiated, $\overline{WP}$ going low will have no effect on any write operation to the status register. The $\overline{WP}$ pin function is blocked when the WPEN bit in the status register is "0". This will allow the user to install the AT25128/256 in a system with the $\overline{WP}$ pin tied to ground and still be able to write to the status register. All $\overline{WP}$ pin functions are enabled when the WPEN bit is set to "1".

SPI Serial Interface
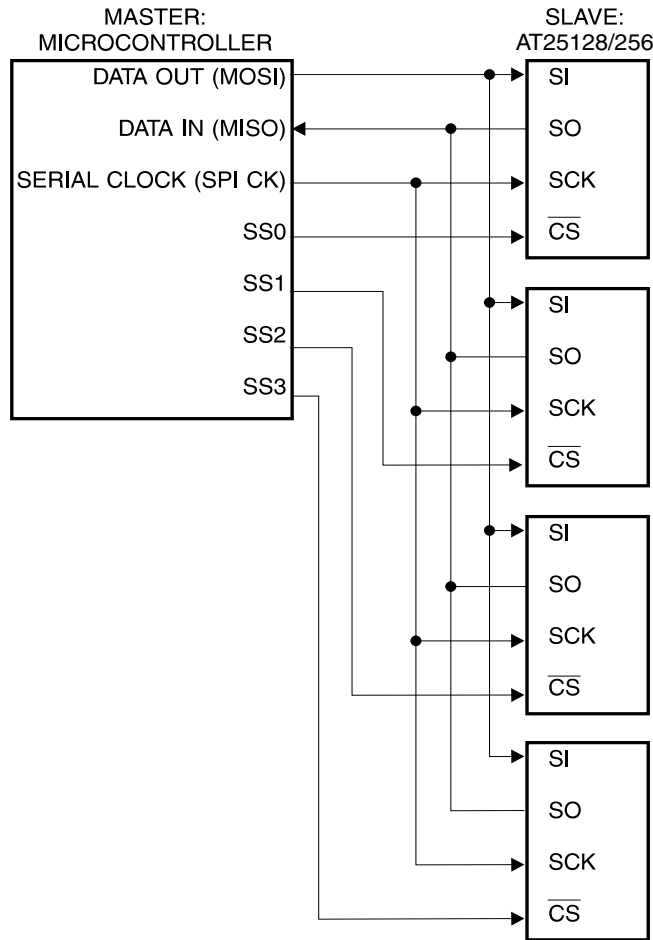
Functional Description

The AT25128/256 is designed to interface directly with the synchronous serial peripheral interface (SPI) of the 6800 type series of microcontrollers.

The AT25128/256 utilizes an 8-bit instruction register. The list of instructions and their operation codes are contained in Table 1. All instructions, addresses, and data are transferred with the MSB first and start with a high-to-low $\overline{CS}$ transition..

Table 1. Instruction Set for the AT25128/256

Instruction Name	Instruction Format	Operation
WREN	0000 X110	Set Write Enable Latch
WRDI	0000 X100	Reset Write Enable Latch
RDSR	0000 X101	Read Status Register
WRSR	0000 X001	Write Status Register
READ	0000 X011	Read Data from Memory Array
WRITE	0000 X010	Write Data to Memory Array

WRITE ENABLE (WREN): The device will power-up in the write disable state when V_{CC} is applied. All programming instructions must therefore be preceded by a Write Enable instruction.

WRITE DISABLE (WRDI): To protect the device against inadvertent writes, the Write Disable instruction disables all programming modes. The WRDI instruction is independent of the status of the $\overline{WP}$ pin.

READ STATUS REGISTER (RDSR): The Read Status Register instruction provides access to the status register. The READY/BUSY and Write Enable status of the device can be determined by the RDSR instruction. Similarly, the Block Write Protection bits indicate the extent of protection employed. These bits are set by using the WRSR instruction.

Table 2. Status Register Format

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
WPEN	X	X	X	BP1	BP0	WEN	$\overline{RDY}$

Table 3. Read Status Register Bit Definition

Bit	Definition
Bit 0 ($\overline{RDY}$)	Bit 0 = 0 ($\overline{RDY}$) indicates the device is READY. Bit 0 = 1 indicates the write cycle is in progress.
Bit 1 (WEN)	Bit 1 = 0 indicates the device *is not* WRITE ENABLED. Bit 1 = 1 indicates the device is WRITE ENABLED.
Bit 2 (BP0)	See Table 4.
Bit 3 (BP1)	See Table 4.
Bits 4 - 6 are 0s when device is not in an internal write cycle.	
Bit 7 (WPEN)	See Table 5.
Bits 0 - 7 are 1s during an internal write cycle.	

WRITE STATUS REGISTER (WRSR): The WRSR instruction allows the user to select one of four levels of protection. The AT25128/256 is divided into four array segments. Top quarter (1/4), top half (1/2), or all of the memory segments can be protected. Any of the data within any selected segment will therefore be READ only. The block write protection levels and corresponding status register control bits are shown in Table 4.

The three bits, BP0, BP1, and WPEN are nonvolatile cells that have the same properties and functions as the regular memory cells (e.g. WREN, t_{WC}, RDSR).

Table 4. Block Write Protect Bits

	Status Register Bits		Array Addresses Protected	
Level	BP1	BP0	AT25128	AT25256
0	0	0	None	None
1(1/4)	0	1	3000 - 3FFF	6000 - 7FFF
2(1/2)	1	0	2000 - 3FFF	4000 - 7FFF
3(All)	1	1	0000 - 3FFF	0000 - 7FFF

The WRSR instruction also allows the user to enable or disable the write protect ($\overline{WP}$) pin through the use of the Write Protect Enable (WPEN) bit. Hardware write protection is enabled when the $\overline{WP}$ pin is low and the WPEN bit is "1". Hardware write protection is disabled when *either* the $\overline{WP}$ pin is high or the WPEN bit is "0." When the device is hardware write protected, writes to the Status Register, including the Block Protect bits and the WPEN bit, and the block-protected sections in the memory array are disabled. Writes are only allowed to sections of the memory which are not block-protected.

NOTE: When the WPEN bit is hardware write protected, it cannot be changed back to "0", as long as the $\overline{WP}$ pin is held low.

Table 5. WPEN Operation

WPEN	WP	WEN	Protected Blocks	Unprotected Blocks	Status Register
0	X	0	Protected	Protected	Protected
0	X	1	Protected	Writable	Writable
1	Low	0	Protected	Protected	Protected
1	Low	1	Protected	Writable	Protected
X	High	0	Protected	Protected	Protected
X	High	1	Protected	Writable	Writable

READ SEQUENCE (READ): Reading the AT25128/256 via the SO (Serial Output) pin requires the following sequence. After the $\overline{CS}$ line is pulled low to select a device, the READ op-code is transmitted via the SI line followed by the byte address to be read (Refer to Table 6). Upon completion, any data on the SI line will be ignored. The data (D7 - D0) at the specified address is then shifted out onto the SO line. If only one byte is to be read, the $\overline{CS}$ line should be driven high after the data comes out. The READ sequence can be continued since the byte address is automatically incremented and data will continue to be shifted out. When the highest address is reached, the address counter will roll over to the lowest address allowing the entire memory to be read in one continuous READ cycle.

WRITE SEQUENCE (WRITE): In order to program the AT25128/256, two separate instructions must be executed. First, the device **must be write enabled** via the Write Enable (WREN) Instruction. Then a Write (WRITE) Instruction may be executed. Also, the address of the memory location(s) to be programmed must be outside the protected address field location selected by the Block Write Protection Level. During an internal write cycle, all commands will be ignored except the RDSR instruction.

A Write Instruction requires the following sequence. After the $\overline{CS}$ line is pulled low to select the device, the WRITE op-code is transmitted via the SI line followed by the byte address and the data (D7 - D0) to be programmed (Refer to Table 6). Programming will start after the $\overline{CS}$ pin is brought high. (The LOW-to-High transition of the $\overline{CS}$ pin must occur during the SCK low time immediately after clocking in the D0 (LSB) data bit.

The READY/BUSY status of the device can be determined by initiating a READ STATUS REGISTER (RDSR) Instruction. If Bit 0 = 1, the WRITE cycle is still in progress. If Bit 0 = 0, the WRITE cycle has ended. Only the READ STATUS REGISTER instruction is enabled during the WRITE programming cycle.

The AT25128/256 is capable of a 64-byte PAGE WRITE operation. After each byte of data is received, the six low order address bits are internally incremented by one; the high order bits of the address will remain constant. If more than 64 bytes of data are transmitted, the address counter will roll over and the previously written data will be overwritten. The AT25128/256 is automatically returned to the write disable state at the completion of a WRITE cycle.
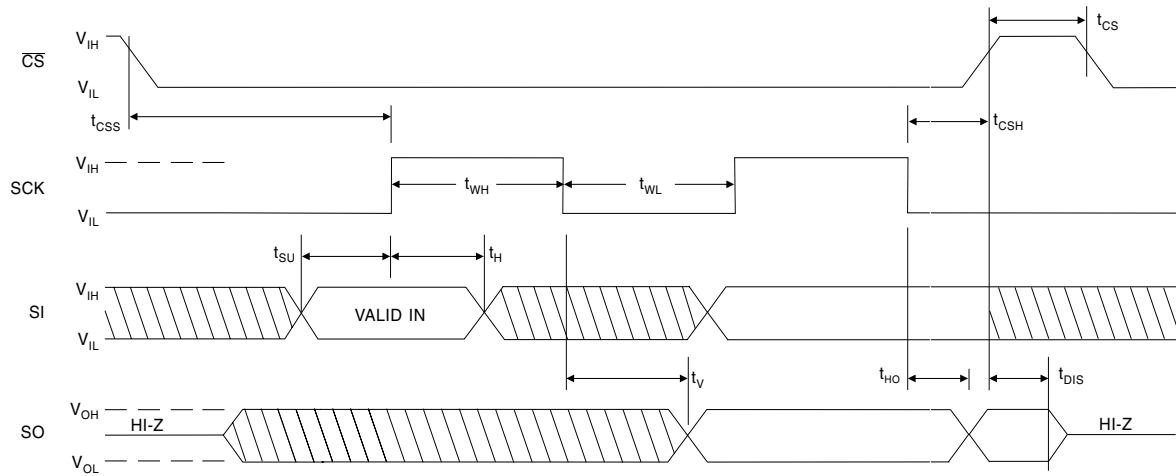
NOTE: If the device is not Write enabled (WREN), the device will ignore the Write instruction and will return to the standby state, when $\overline{CS}$ is brought high. A new CS falling edge is required to re-initiate the serial communication.

Table 6. Address Key

Address	AT25128	AT25256
A_N	$A_{13} - A_0$	$A_{14} - A_0$
Don't Care Bits	$A_{15} - A_{14}$	A_{15}

Timing Diagrams (for SPI Mode 0 (0, 0))

Synchronous Data Timing

WREN Timing

WRDI Timing

RDSR Timing

CS

SCK
0 1 2 3 4 5 6 7 8 9 10 11 12 13 14

SI
INSTRUCTION

SO
HIGH IMPEDANCE

DATA OUT
7 6 5 4 3 2 1 0
MSB

WRSR Timing

CS

SCK
0 1 2 3 4 5 6 7 8 9 10 11 12 13 14 15

SI
INSTRUCTION

DATA IN
7 6 5 4 3 2 1 0

SO
HIGH IMPEDANCE

READ Timing

CS

SCK
0 1 2 3 4 5 6 7 8 9 10 11 20 21 22 23 24 25 26 27 28 29 30

SI
INSTRUCTION

BYTE ADDRESS
15 14 13 ... 3 2 1 0

SO
HIGH IMPEDANCE

DATA OUT
7 6 5 4 3 2 1 0
MSB

WRITE Timing

CS

SCK 0 1 2 3 4 5 6 7 8 9 10 11 20 21 22 23 24 25 26 27 28 29 30 31

SI INSTRUCTION BYTE ADDRESS 15 14 13 ... 3 2 1 0 DATA IN 7 6 5 4 3 2 1 0

SO HIGH IMPEDANCE

HOLD Timing

CS

SCK t_{CD} t_{CD}

HOLD t_{HD} t_{HD}

SO t_{HZ} t_{LZ}

AT25128 Ordering Information

Ordering Code	Package	Operation Range
AT25128-10PI-2.7	8P3	Industrial
AT25128N-10SI-2.7	8S1	(-40°C to 85°C)
AT25128W-10SI-2.7	8S2	
AT25128-10UI-2.7	8U4	
AT25128N1-10SI-2.7	16S1	
AT25128T1-10TI-2.7	14A2	
AT25128-10PI-1.8	8P3	Industrial
AT25128N-10SI-1.8	8S1	(-40°C to 85°C)
AT25128W-10SI-1.8	8S2	
AT25128-10UI-1.8	8U4	
AT25128N1-10SI-1.8	16S1	
AT25128T1-10TI-1.8	14A2	

Note: For 2.7V devices used in the 4.5V to 5.5V range, please refer to performance values in the AC and DC Characteristics tables.

Package Type	
8P3	8-lead, 0.300" Wide, Plastic Dual In-line Package (PDIP)
8S1	8-lead, 0.150" Wide, Plastic Gull Wing Small Outline Package (JEDEC SOIC)
8S2	8-lead, 0.200" Wide, Plastic Gull Wing Small Outline Package (EIAJ SOIC)
8U4	8-ball, die Ball Grid Array Package (dBGA)
16S1	16-lead, 0.150" Wide, Plastic Gull Wing Small Outline Package (JEDEC SOIC)
14A2	14-lead, 0.170" Wide, Thin Shrink Small Outline Package (TSSOP)
Options	
-2.7	Low-voltage (2.7V to 5.5V)
-1.8	Low-voltage (1.8V to 5.5V)

AT25256 Ordering Information

Ordering Code	Package	Operation Range
AT25256-10PI-2.7	8P3	Industrial
AT25256W-10SI-2.7	8S2	(-40°C to 85°C)
AT25256-10CI-2.7	8CN3	
AT25256-10UI-2.7	8U3	
AT25256T2-10TI-2.7	20A2	
AT25256-10PI-1.8	8P3	Industrial
AT25256W-10SI-1.8	8S2	(-40°C to 85°C)
AT25256-10CI-1.8	8CN3	
AT25256-10UI-1.8	8U3	
AT25256T2-10TI-1.8	20A2	

Note: For 2.7V devices used in the 4.5V to 5.5V range, please refer to performance values in the AC and DC Characteristics tables.

Package Type	
8P3	8-lead, 0.300" Wide, Plastic Dual In-line Package (PDIP)
8S2	8-lead, 0.200" Wide, Plastic Gull Wing Small Outline Package (EIAJ SOIC)
8CN3	8-lead, 0.230" Wide, Leadless Array Package (LAP)
8U3	8-ball, die Ball Grid Array Package (dBGA)
20A2	20-lead, 0.170" Wide, Thin Shrink Small Outline Package (TSSOP)
Options	
-2.7	Low-voltage (2.7V to 5.5V)
-1.8	Low-voltage (1.8V to 5.5V)

Packaging Information

8P3 – PDIP

Top View

End View

Side View

b3
4 PLCS
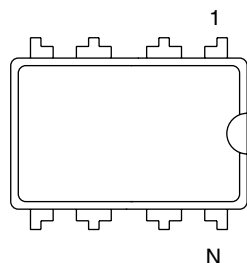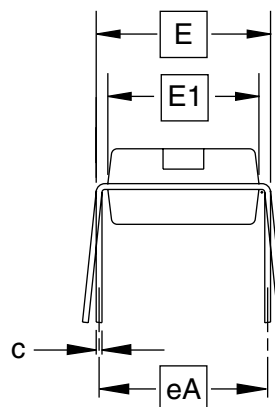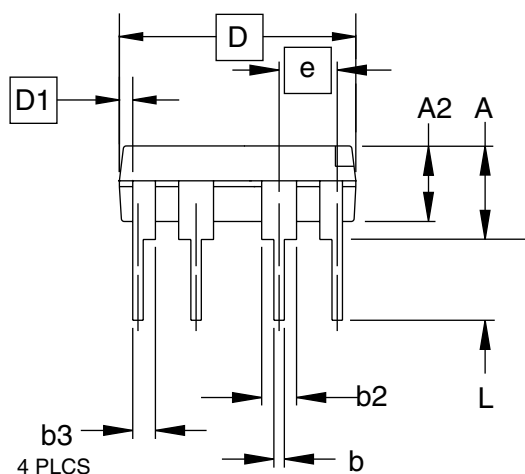
COMMON DIMENSIONS
(Unit of Measure = inches)

SYMBOL	MIN	NOM	MAX	NOTE
A			0.210	2
A2	0.115	0.130	0.195	
b	0.014	0.018	0.022	5
b2	0.045	0.060	0.070	6
b3	0.030	0.039	0.045	6
c	0.008	0.010	0.014	
D	0.355	0.365	0.400	3
D1	0.005			3
E	0.300	0.310	0.325	4
E1	0.240	0.250	0.280	3
e	0.100 BSC			
eA	0.300 BSC			4
L	0.115	0.130	0.150	2

Notes: 1. This drawing is for general information only; refer to JEDEC Drawing MS-001, Variation BA for additional information.
2. Dimensions A and L are measured with the package seated in JEDEC seating plane Gauge GS-3.
3. D, D1 and E1 dimensions do not include mold Flash or protrusions. Mold Flash or protrusions shall not exceed 0.010 inch.
4. E and eA measured with the leads constrained to be perpendicular to datum.
5. Pointed or rounded lead tips are preferred to ease insertion.
6. b2 and b3 maximum dimensions do not include Dambar protrusions. Dambar protrusions shall not exceed 0.010 (0.25 mm).

01/09/02

AIMEL 2325 Orchard Parkway San Jose, CA 95131	**TITLE** **8P3**, 8-lead, 0.300" Wide Body, Plastic Dual In-line Package (PDIP)	**DRAWING NO.** 8P3 / **REV.** B

8S1 – JEDEC SOIC
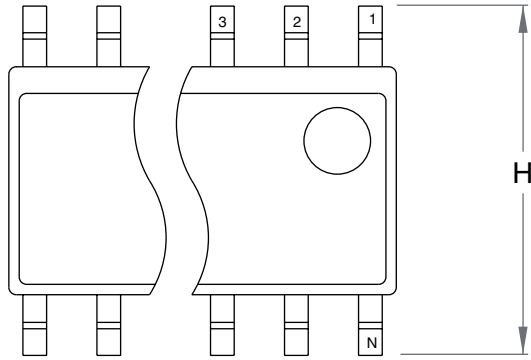
Top View
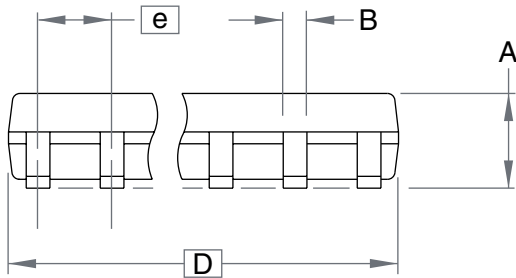
Side View
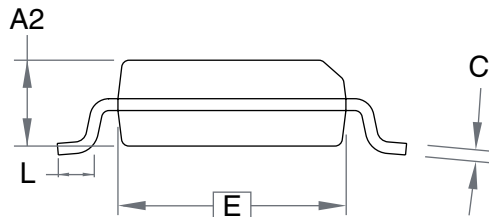
End View

COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	–	–	1.75	
B	–	–	0.51	
C	–	–	0.25	
D	–	–	5.00	
E	–	–	4.00	
e	1.27 BSC			
H	–	–	6.20	
L	–	–	1.27	

Note: This drawing is for general information only. Refer to JEDEC Drawing MS-012 for proper dimensions, tolerances, datums, etc.

10/10/01

		TITLE	DRAWING NO.	REV.
ATMEL	2325 Orchard Parkway San Jose, CA 95131	**8S1**, 8-lead (0.150" Wide Body), Plastic Gull Wing Small Outline (JEDEC SOIC)	8S1	A

8S2 – EIAJ SOIC
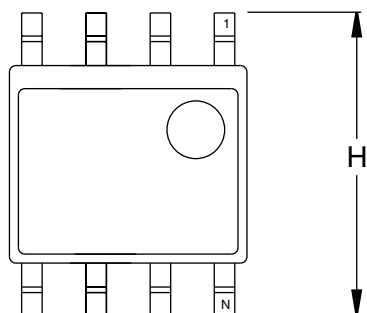
Top View
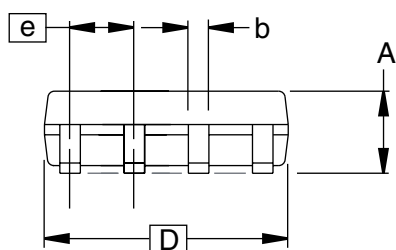
Side View
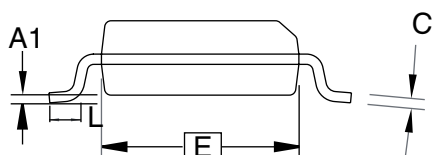
End View

COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	1.78		2.03	
A1	0.05		0.33	
b	0.35		0.51	5
C	0.18		0.25	5
D	5.13		5.38	
E	5.13		5.41	2, 3
H	7.62		8.38	
L	0.51		0.89	
e		1.27 BSC		4

Notes: 1. This drawing is for general information only; refer to EIAJ Drawing EDR-7320 for additional information.
2. Mismatch of the upper and lower dies and resin burrs aren't included.
3. It is recommended that upper and lower cavities be equal. If they are different, the larger dimension shall be regarded.
4. Determines the true geometric position.
5. Values b,C apply to pb/Sn solder plated terminal. The standard thickness of the solder layer shall be 0.010 +0.010/-0.005 mm.

5/2/02

	2325 Orchard Parkway San Jose, CA 95131	**TITLE** **8S2**, 8-lead, 0.209" Body, Plastic Small Outline Package (EIAJ)	DRAWING NO. 8S2	REV. B

8CN3 – LAP
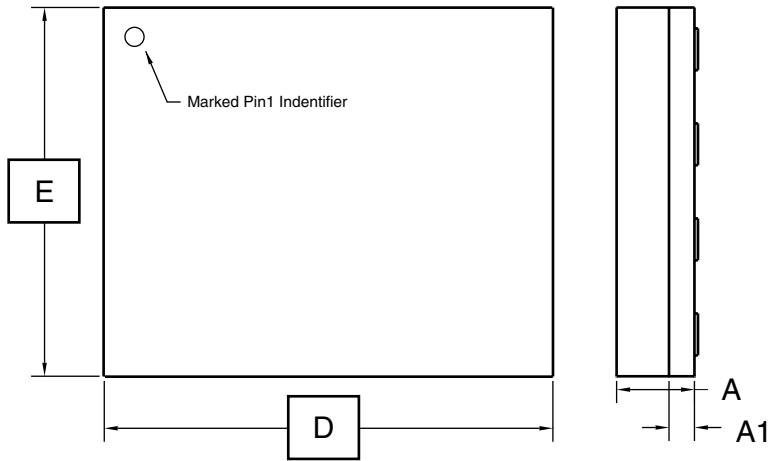
Top View

Side View

Bottom View

0.10 mm TYP
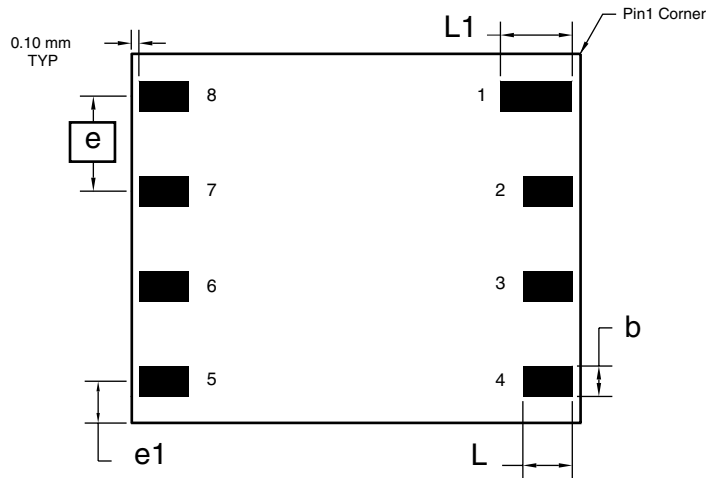
Note: 1. Metal Pad Dimensions.

COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	0.94	1.04	1.14	
A1	0.30	0.34	0.38	
b	0.36	0.41	0.46	1
D	5.89	5.99	6.09	
E	4.83	4.93	5.03	
e	1.27 BSC			
e1	0.56 REF			
L	0.62	0.67	0.72	1
L1	0.92	0.97	1.02	1

11/14/01

	TITLE	DRAWING NO.	REV.
ATMEL 2325 Orchard Parkway San Jose, CA 95131	**8CN3**, 8-lead, (6 x 5 x 1.04 mm Body), Lead Pitch 1.27 mm, Leadless Array Package (LAP)	8CN3	A

8U3 – dBGA
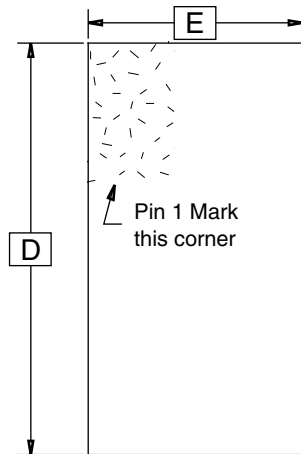
Top View
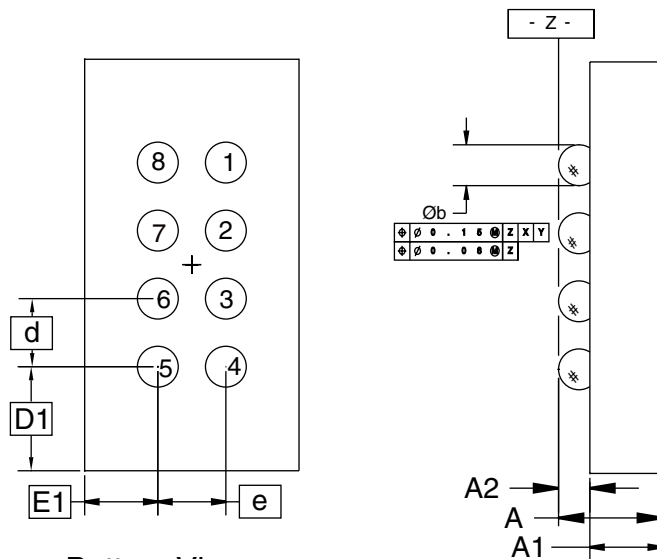
Bottom View

Side View

COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
D			3.86	
D1		0.81 TYP		
E			2.95	
E1		1.10 TYP		
e		0.75 TYP		
d		0.75 TYP		
A		0.90 REF		
A1	0.49	0.52	0.55	
A2	0.35	0.38	0.41	
Øb	0.47	0.50	0.53	

Notes: 1. This drawing is for general information only. No JEDEC Drawing to refer to for additional information.
2. Dimension is measured at the maximum solder ball diameter, parallel to primary datum Z.

01/09/02

	TITLE	DRAWING NO.	REV.
AMEL 2325 Orchard Parkway San Jose, CA 95131	**8U3**, 8-ball 0.75 pitch, Die Ball Grid Array Package (dBGA) AT25256 (AT19874)	8U3	A

8U4 – dBGA

E

D

Pin 1 Mark
this corner

Top View

- Z -

Bottom View

8 1

7 2

+

6 3

5 4

d

D1

E1   e

Øb

| ⊕ | Ø 0 . 1 5 Ⓜ | Z | X | Y |
| ⊕ | Ø 0 . 0 8 Ⓜ | Z | | |

A2

A

A1

Side View

COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
D			3.73	
D1		0.74 TYP		
E			2.21	
E1		0.73 TYP		
e		0.75 TYP		
d		0.75 TYP		
A		0.90 REF		
A1	0.49	0.52	0.55	
A2	0.35	0.38	0.41	
Øb	0.47	0.50	0.53	

Notes: 1. This drawing is for general information only. No JEDEC Drawing to refer to for additional information.
　　　　 2. Dimension is measured at the maximum solder ball diameter, parallel to primary datum Z.

01/09/02

	TITLE	DRAWING NO.	REV.
AT

MEL
®
2325 Orchard Parkway
San Jose, CA 95131 | **8U4**, 8-ball 0.75 pitch, Die Ball Grid Array
Package (dBGA) AT25128 (AT19875) | 8U4 | A |

16S1 – JEDEC SOIC

Top View

H

Side View

e   B   A

D

End View

A2   C

L   E
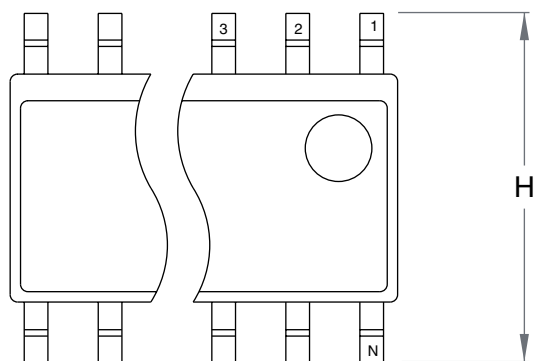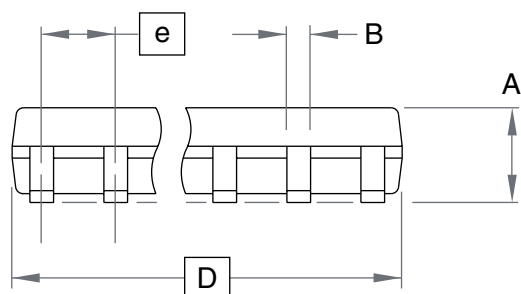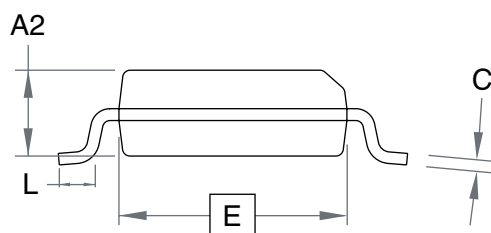
COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	1.35	–	1.75	
B	0.33	–	0.51	5
C	0.19	–	0.25	
D	9.80	–	10.00	2
E	3.80	–	4.00	3
e	1.27 BSC			
H	5.80	–	6.20	4
L	0.40	–	1.27	

Notes: 1. This drawing is for general information only; refer to JEDEC Drawing MS-012 for proper dimensions, tolerances, datums, etc.
  2. Dimension D does not include mold Flash, protrusions or gate burrs. Mold Flash, protrusions and gate burrs shall not exceed 0.15 mm (0.006 in) per side.
  3. Dimension E does not include inter-lead Flash or protrusions. Inter-lead Flash and protrusions shall not exceed 0.25 mm (0.010 in) per side.
  4. L is the length of terminal for soldering to a substrate.
  5. The lead width B, as measured 0.36 mm (0.014 in) or greater above the seating plane, shall not exceed a maximum value of 0.61 mm (0.024 in).

10/15/01

	TITLE	DRAWING NO.	REV.
ATMEL 2325 Orchard Parkway San Jose, CA 95131	**16S1**, 16-lead, 0.150" Body, Plastic Gull Wing Small Outline (SOIC)	16S1	A

14A2 – TSSOP

b

E E1

Top View

A D A2

Side View

End View

L

L1

e
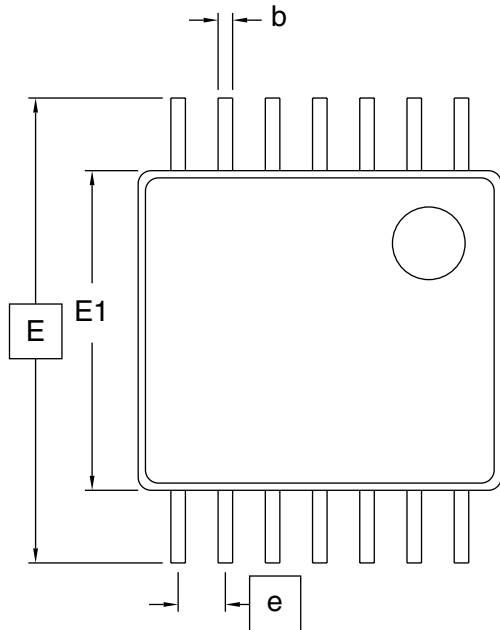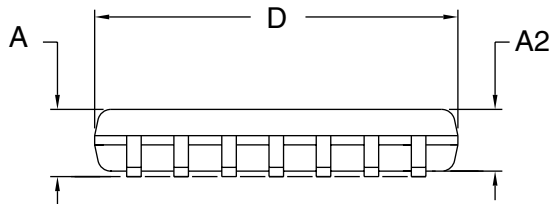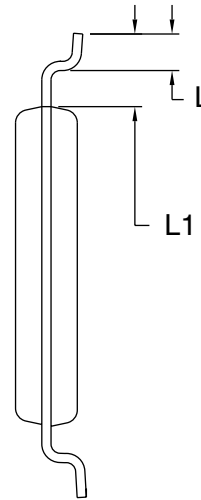
COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
D	4.90	5.00	5.10	2, 5
E		6.40 BSC		
E1	4.30	4.40	4.50	3, 5
A			1.20	
A2	0.80	1.00	1.05	
b	0.19		0.30	4
e		0.65 BSC		
L	0.45	0.60	0.75	
L1		1.00 REF		

Notes: 1. This drawing is for general information only. Please refer to JEDEC Drawing MO-153, Variation AB-1 for additional information.
2. Dimension "D" does not include mold Flash, protrusions or gate burrs. Mold Flash, protrusions and gate burrs shall not exceed 0.15 mm (0.006 in) per side.
3. Dimension "E1" does not include inter-lead Flash or protrusions. Inter-lead Flash and protrusions shall not exceed 0.25 mm (0.010 in) per side.
4. Dimension "b" does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the "b" dimension at maximum material condition. Dambar cannot be located on the lower radius of the foot. Minimum space between protrusion and adjacent lead is 0.07 mm.
5. Dimension "D" and "E1" to be determined at Datum Plane H.

12/28/01

	TITLE	DRAWING NO.	REV.
2325 Orchard Parkway San Jose, CA 95131	**14A2**,14-lead (4.4 x 5 mm Body), 0.65 Pitch, Thin Shrink Small Outline Package (TSSOP)	14A2	A

20A2 – TSSOP
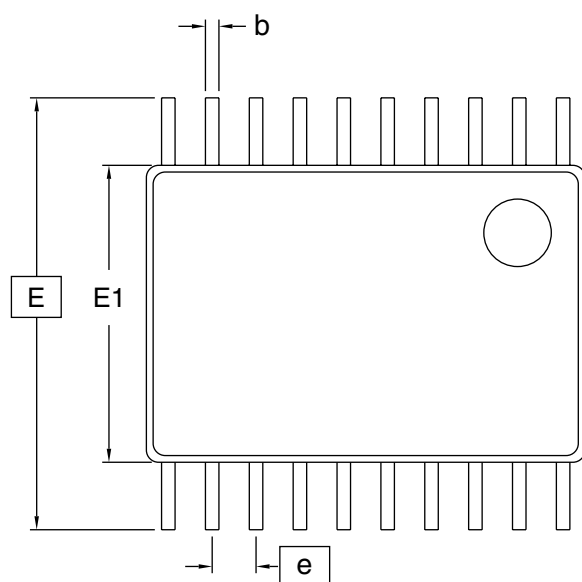
Top View
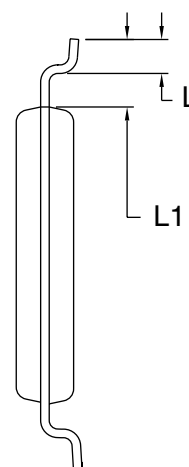
End View
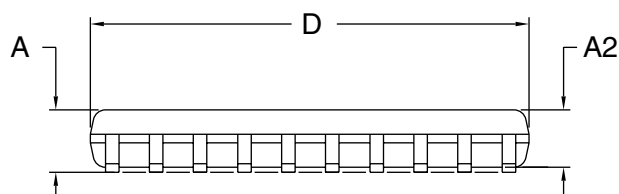
Side View

COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
D	6.40	6.50	6.60	2, 5
E	6.40 BSC			
E1	4.30	4.40	4.50	3, 5
A	–	–	1.20	
A2	0.80	1.00	1.05	
b	0.19	–	0.30	4
e	0.65 BSC			
L	0.45	0.60	0.75	
L1	1.00 REF			

Notes: 1. This drawing is for general information only. Please refer to JEDEC Drawing MO-153, Variation AC, for additional information.
2. Dimension D does not include mold Flash, protrusions or gate burrs. Mold Flash, protrusions and gate burrs shall not exceed 0.15 mm (0.006 in) per side.
3. Dimension E1 does not include inter-lead Flash or protrusions. Inter-lead Flash and protrusions shall not exceed 0.25 mm (0.010 in) per side.
4. Dimension b does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the b dimension at maximum material condition. Dambar cannot be located on the lower radius of the foot. Minimum space between protrusion and adjacent lead is 0.07 mm.
5. Dimension D and E1 to be determined at Datum Plane H.

6/3/02

	TITLE	DRAWING NO.	REV.
ATMEL 2325 Orchard Parkway San Jose, CA 95131	**20A2**, 20-lead (4.4 x 6.5 mm Body), 0.65 pitch, Thin Shrink Small Outline Package (TSSOP)	20A2	C

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